TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

2SK3301

Switching Regulatorand DC-DC Converter Applications

• Low drain-source ON resistance: RDS (ON) = 15 Ω (typ.)

• High forward transfer admittance: $|Y_{fs}| = 0.65 S$ (typ.)

• Low leakage current: $IDSS = 100 \mu A \text{ (max) (V}_{DS} = 720 \text{ V)}$

• Enhancement mode: $V_{th} = 2.4 \sim 3.4 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | nbol Rating | | |
|---|-------------------|------------------|-------------|----|--|
| Drain-source voltage | | V_{DSS} | 900 | V | |
| Drain-gate voltage (R _{GS} = 20 k Ω) | | V_{DGR} | 900 | V | |
| Gate-source voltage | | V _{GSS} | ±30 | V | |
| Drain current | DC (Note 1) | ID | 1 | А | |
| | Pulse (Note 1) | I _{DP} | 2 | | |
| Drain power dissipation (Tc = 25°C) | | P _D | 20 | W | |
| Single pulse avalanche energy (Note 2) | | E _{AS} | 140 | mJ | |
| Avalanche current | | I _{AR} | 1 | Α | |
| Repetitive avalanche energy (Note 3) | | E _{AR} | 2.0 | mJ | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case | R _{th (ch-c)} | 6.25 | °C/W |
| Thermal resistance, channel to ambient | R _{th (ch-a)} | 125 | °C/W |

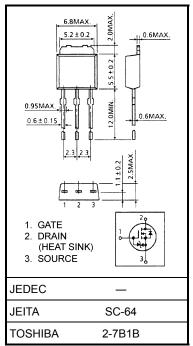
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 257 mH, $R_G = 25 \Omega$, $I_{AR} = 1 \text{ A}$

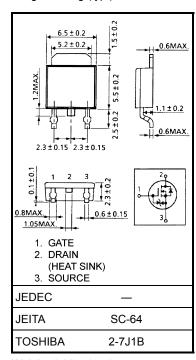
Note 3: Repetitive rating: pulse width limited by max junction temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight: 0.36 g (typ.)



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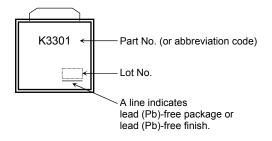
Electrical Characteristics (Ta = 25°C)

| Char | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|-------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage cui | rent | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±10 | μΑ |
| Gate-source brea | Gate-source breakdown voltage | | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$ | ±30 | _ | _ | V |
| Drain cut-off curr | ent | I _{DSS} | $V_{DS} = 720 \text{ V}, V_{GS} = 0 \text{ V}$ | _ | _ | 100 | μΑ |
| Drain-source bre | akdown voltage | V (BR) DSS | $I_D = 10$ mA, $V_{GS} = 0$ V | 900 | _ | _ | V |
| Gate threshold voltage | | V _{th} | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ | 2.4 | _ | 3.4 | V |
| Drain-source ON resistance | | R _{DS} (ON) | V _{GS} = 10 V, I _D = 0.5 A | _ | 15 | 20 | Ω |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 0.5 A | 0.3 | 0.65 | _ | S |
| Input capacitance | e | C _{iss} | | _ | 165 | | pF |
| Reverse transfer capacitance | | C _{rss} | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _ | 6 | _ | pF |
| Output capacitance | | C _{oss} | | _ | 21 | _ | pF |
| Switching time | Rise time | t _r | 10 V VGS VOUT CO VOUT | _ | 15 | _ | |
| | Turn-on time | t _{on} | | _ | 60 | _ | no |
| | Fall time | t _f | | _ | 40 | _ | ns |
| | Turn-off time | t _{off} | Duty \leq 1%, $t_W = 10 \mu s$ | | 110 | _ | L |
| Total gate charge (gate-source plus gate-drain) | | Qg | $V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$ | | 6 | _ | nC |
| Gate-source charge | | Q _{gs} | | | 3 | | nC |
| Gate-drain ("miller") charge | | Q _{gd} | | | 3 | | nC |

Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I _{DR} | _ | _ | _ | 1 | А |
| Pulse drain reverse current (Note 1) | I _{DRP} | _ | _ | _ | 2 | Α |
| Forward voltage (diode) | V _{DSF} | I _{DR} = 1 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | $I_{DR} = 1 A$, $V_{GS} = 0 V$ | | 1300 | | ns |
| Reverse recovery charge | Qrr | dl _{DR} /dt = 100 A/μs | _ | 1.95 | | μС |

Marking



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20070701-EN

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